

**Silicon PNP Power Transistors**

**2SA1102**

**DESCRIPTION**

- With TO-3PN package
- Complement to type 2SC2577
- High current capability
- High power dissipation

**APPLICATIONS**

- Audio power amplifier applications
- DC-DC converters

**PINNING**

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

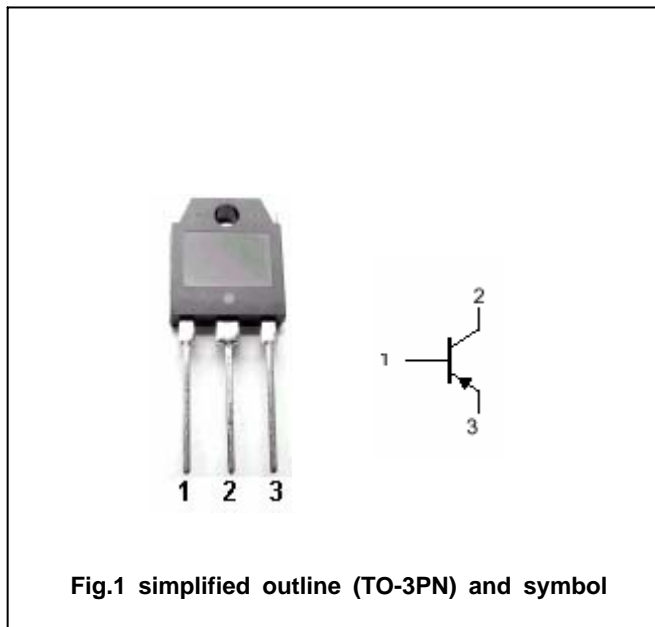


Fig.1 simplified outline (TO-3PN) and symbol

**Absolute maximum ratings(Ta= )**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-80	V
$V_{CEO}$	Collector-emitter voltage	Open base	-80	V
$V_{EBO}$	Emitter-base voltage	Open collector	-6	V
$I_C$	Collector current		-6	A
$P_C$	Collector power dissipation	$T_C=25$	60	W
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-55~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-25mA ; I <sub>B</sub> =0	-80			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.5	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-3A; I <sub>B</sub> =-0.3A			-1.8	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-80V; I <sub>E</sub> =0			-100	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-6V; I <sub>C</sub> =0			-100	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-2A ; V <sub>CE</sub> =4V	50			
f <sub>T</sub>	Transition frequency	I <sub>E</sub> =1A ; V <sub>CE</sub> =-12V		20		MHz

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PACKAGE OUTLINE

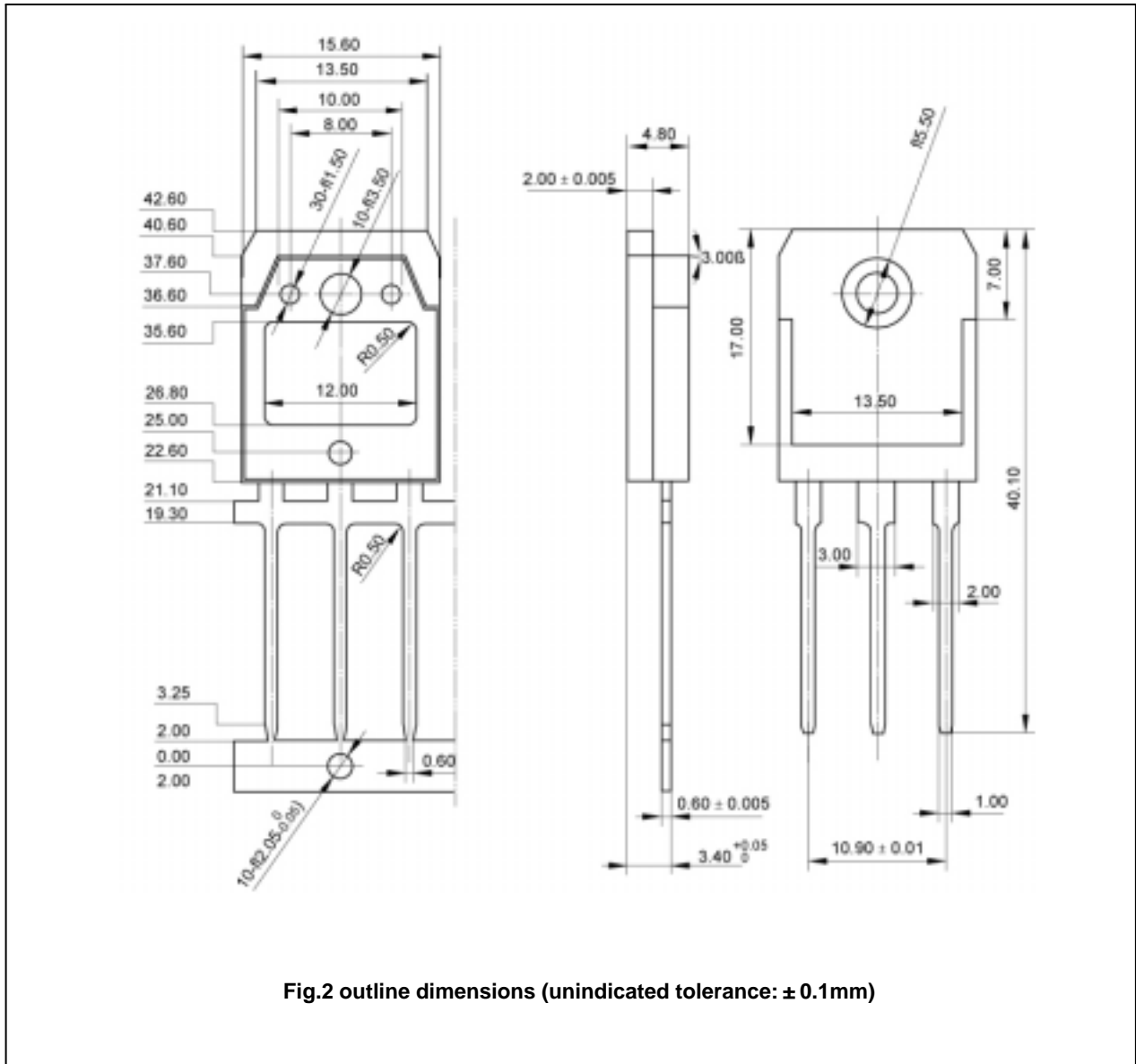


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)